

# **PBHV8118T**

180 V, 1 A NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

Rev. 01 — 7 May 2010 Product data

Product data sheet

## **Product profile**

### 1.1 General description

NPN high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

#### 1.2 Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- AEC-Q101 qualified
- Small SMD plastic package

### 1.3 Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive power management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	180	V
I <sub>C</sub>	collector current		-	-	1	Α
h <sub>FE</sub>	DC current gain	$V_{CE} = 10 \text{ V};$ $I_C = 50 \text{ mA}$	<u>11</u> 100	250	-	

<sup>[1]</sup> Pulse test:  $t_D \le 300 \ \mu s$ ;  $\delta \le 0.02$ .



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# 2. Pinning information

Table 2. Pinning

Table 2.	Filling		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter		3
3	collector	1 2	1 — 2
			sym021

# 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBHV8118T	-	plastic surface-mounted package; 3 leads	SOT23		

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PBHV8118T	LZ*

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

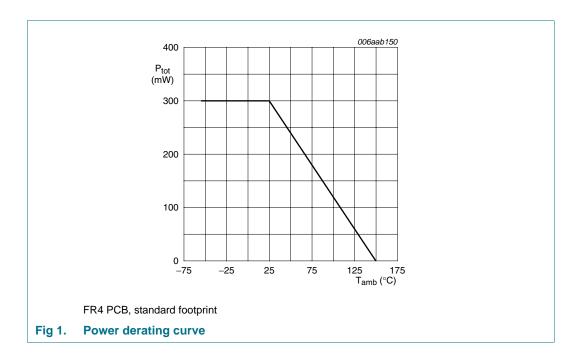
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# 5. Limiting values

**Table 5.** Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	400	V
$V_{CEO}$	collector-emitter voltage	open base	-	180	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	1	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	2	Α
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	400	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> _	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		<b>–55</b>	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C
·		· · · · · · · · · · · · · · · · · · ·	·	·	·

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



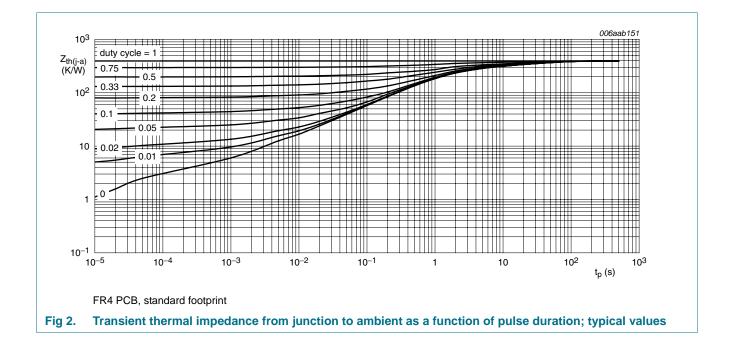
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### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	417	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	70	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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### 7. Characteristics

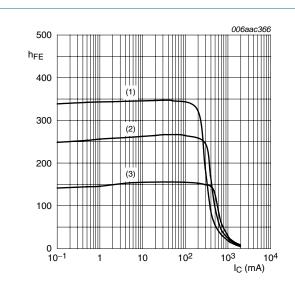
**Table 7. Characteristics** 

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = 144 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
	current	$V_{CB} = 144 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	10	μА
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = 144 \text{ V}; V_{BE} = 0 \text{ V}$	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 4 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V	[1]			
		$I_C = 50 \text{ mA}$	100	250	-	
		$I_C = 100 \text{ mA}$	100	250	-	
		$I_C = 0.5 A$	50	100	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 100 \text{ mA}; I_B = 10 \text{ mA}$	<u>[1]</u> -	40	60	mV
		$I_C = 100 \text{ mA}; I_B = 20 \text{ mA}$	<u>[1]</u> -	33	50	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 0.5 \text{ A}; I_B = 100 \text{ mA}$	<u>[1]</u> _	1	1.2	V
t <sub>d</sub>	delay time	$V_{CC} = 6 \text{ V}; I_C = 0.5 \text{ A};$	-	7	-	ns
t <sub>r</sub>	rise time	$I_{Bon} = 0.1 \text{ A}; I_{Boff} = -0.1 \text{ A}$	-	565	-	ns
t <sub>on</sub>	turn-on time		-	572	-	ns
t <sub>s</sub>	storage time		-	1320	-	ns
t <sub>f</sub>	fall time		-	740	-	ns
t <sub>off</sub>	turn-off time		-	2060	-	ns
f <sub>T</sub>	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	-	30	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	5.7	-	pF
Ce	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = i_c = 0 \text{ A};$ f = 1 MHz	-	150	-	pF

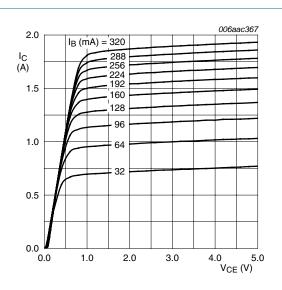
<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

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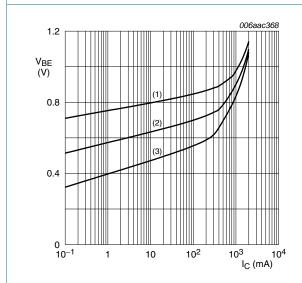
- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

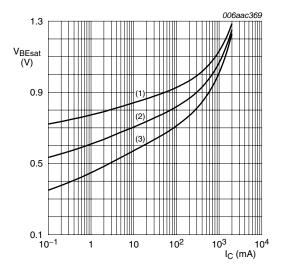
Fig 4. Collector current as a function of collector-emitter voltage; typical values





- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3) T<sub>amb</sub> = 100 °C

Fig 5. Base-emitter voltage as a function of collector current; typical values

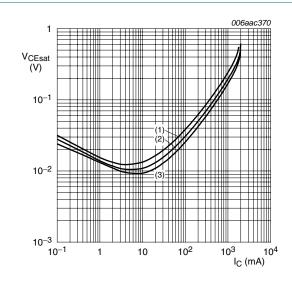


 $I_{\rm C}/I_{\rm B}=5$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

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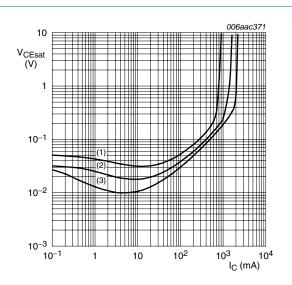
$$I_{\rm C}/I_{\rm B}=5$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



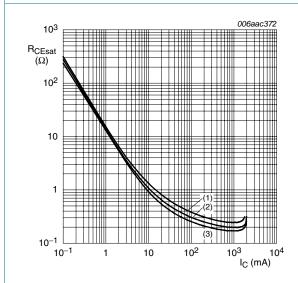
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 20$$

(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



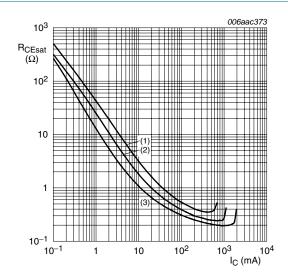
$$I_C/I_B = 5$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Collector-emitter saturation resistance as a function of collector current; typical values



(1) 
$$I_C/I_B = 20$$

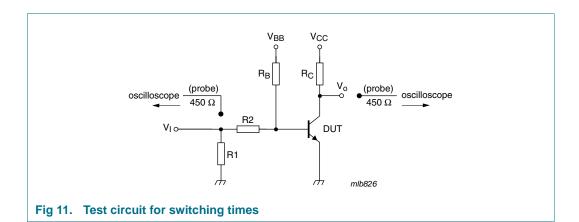
(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

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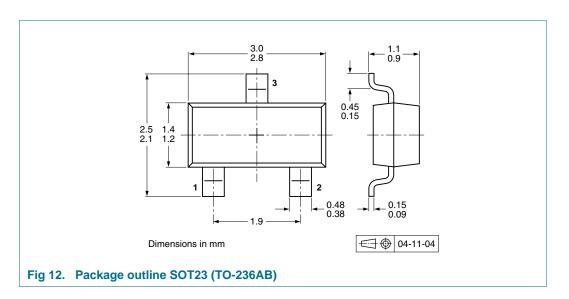
### 8. Test information



### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



# 10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PBHV8118T	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

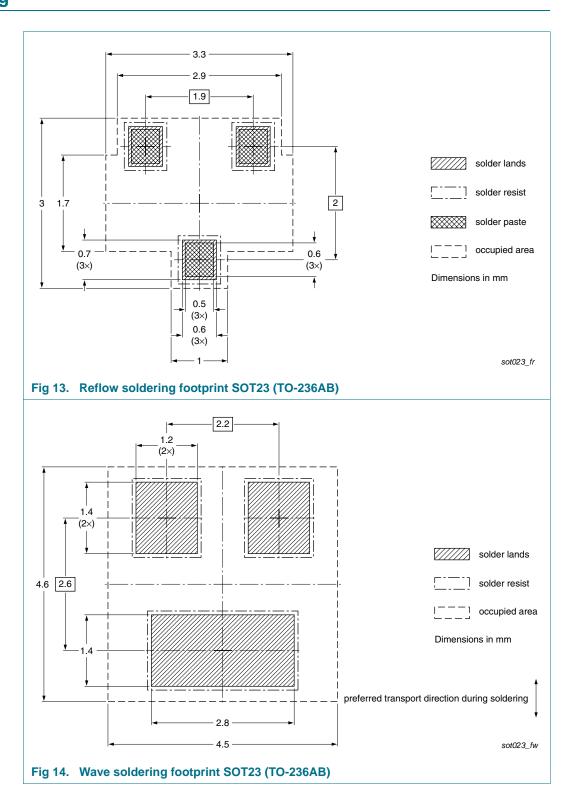
[1] For further information and the availability of packing methods, see Section 14.

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# 11. Soldering



## 180 V, 1 A NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

# 12. Revision history

### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8118T v.1	20100507	Product data sheet	-	-

### 180 V, 1 A NPN high-voltage low V<sub>CEsat</sub> (BISS) transistor

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#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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